

PC8110xNSZ Series

DIP 4pin High Speed under High Load Resistance Photocoupler



■ Description

PC8110xNSZ Series contains an IRED optically coupled to a phototransistor built-in schottky barrier diode.

It is packaged in a 4-pin DIP, and SMT gullwing lead-form option.

Input-output isolation voltage(rms) is 5.0kV. CTR is 50% to 400% at input current of 5mA.

■ Features

- 1. 4pin DIP package
- Double transfer mold package (Ideal for Flow Soldering)
- 3. High speed response at turn-off time due to built-in schottky barrier diode (at saturation mode)
- 4. High isolation voltage between input and output (V_{iso(rms)}: 5kV)

■ Agency approvals/Compliance

- Recognized by UL1577 (Double protection isolation), file No. E64380 (as model No. PC8110)
- 2. Package resin: UL flammability grade (94V-0)

■ Applications

1. Home appliances

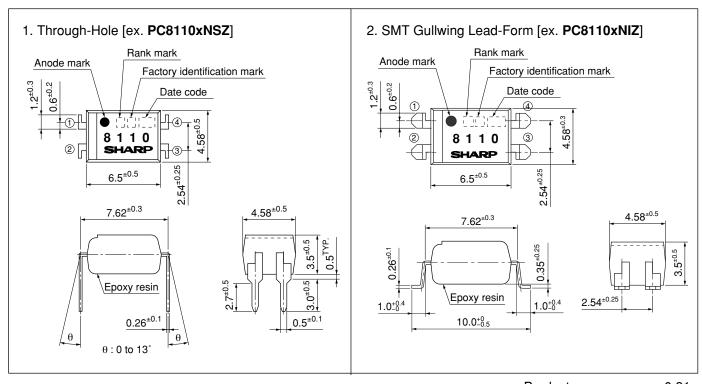


■ Internal Connection Diagram

Schottky barrier diode 1 Anode 3 Cathode 2 Emitter 5 Collector

■ Outline Dimensions

(Unit: mm)



Product mass: approx. 0.21g



Date code (2 digit)

	1st o	digit		2nd digit	
	Year of p	roduction		Month of production	
A.D.	Mark	A.D	Mark	Month	Mark
1990	A	2002	P	January	1
1991	В	2003	R	February	2
1992	С	2004	S	March	3
1993	D	2005	T	April	4
1994	Е	2006	U	May	5
1995	F	2007	V	June	6
1996	Н	2008	W	July	7
1997	J	2009	X	August	8
1998	K	2010	A	September	9
1999	L	2011	В	October	0
2000	M	2012	С	November	N
2001	N	:	:	December	D

repeats in a 20 year cycle

Factory identification mark

Factory identification Mark	Country of origin	
no mark	- Japan	
	Indonesia	
$\overline{\hspace{1cm}}$	Philippines	
	China	

^{*} This factory marking is for identification purpose only.

Please contact the local SHARP sales representative to see the actural status of the production.

Rank mark

Refer to the Model Line-up table



■ Absolute Maximum Ratings

■ Absolute Maximum Ratings $(T_a=25^{\circ}C_a=10^{\circ}C_a=1$						
	Parameter	Symbol	Rating	Unit		
	Forward current	I_{F}	50	mA		
Input	*1 Peak forward current	I_{FM}	1.0	A		
In	Reverse voltage	V_R	6	V		
	Power dissipation	P	70	mW		
	Collector-emitter voltage	V_{CEO}	70	V		
Output	Emitter-collector voltage	V_{ECO}	0.1	V		
Out	Collector current	I_C	30	mA		
	Collector power dissipation	P_{C}	150	mW		
	Γotal power dissipation	P_{tot}	200	mW		
*2]	solation voltage	V _{iso (rms)}	5.0	kV		
Operating temperature		T_{opr}	-30 to +100	°C		
	Storage temperature	T _{stg}	-55 to +125	°C		
*3 (Soldering temperature	T_{sol}	260	°C		

■ Electro-optical Characteristics

 $(T_a=25^{\circ}C)$

	(12-2							(1_a-25C)	
	Parameter			Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Forward voltag		age	V_F I_F =20mA		_	1.2	1.4	V	
Lamint	Input	Peak forward	eak forward voltage		I_{FM} =0.5A	_	_	3.0	V
Input		Reverse Current		I_R	$V_R=4V$	_	-	10	μΑ
	7	Terminal capacitance		C_t	V=0, f=1kHz	_	30	250	pF
Outmut	(Collector darl	k current	I_{CEO}	$V_{CE}=50V, I_{F}=0$	_	-	100	nA
Output	*4 (Collector-emitter brea	akdown voltage	BV_{CEO}	$I_{C}=0.1 \text{mA}, I_{F}=0$	70	_	_	V
		Collector current		I_{C}	$I_F=5mA, V_{CE}=5V$	2.5	_	20	mA
	C	Collector-emitter saturation voltage		$V_{\text{CE (sat)}}$	$I_F=20\text{mA}, I_C=1\text{mA}$	_	0.15	0.35	V
	I	Isolation resistance		$R_{\rm ISO}$	DC500V, 40 to 60%RH	5×10 ¹⁰	1011	_	Ω
	Floating ca	Floating capa	citance	$C_{\rm f}$	V=0, f=1MHz	-	0.6	1.0	pF
		Not saturated	Rise time	t_r	V_{CE} =2V, I_{C} =2mA, R_{L} =100 Ω	_	3	20	
Transfer			Fall time	t_{f}		-	2	10	
charac- teristics	me	Saturated 1	Turn-on time	ton	V_{CC} =5V, I_C =20mA, R_L =10k Ω	_	2	13	
toriotics	se ti		Storage time	t_s			9	50	
	Response		Turn-off time	$t_{\rm off}$		_	23	90	μs
	Res	Saturated 2	Turn-on time	ton	V_{CC} =5V, I_C =20mA, R_L =100k Ω	_	3	13	
			Storage time	t _s		_	10	50	
			Turn-off time	$t_{\rm off}$		_	27	100	

^{*4} The collector-emitter voltage has negative resistance characteristics since this device has built-in base-emitter resistor. Therefore, please be careful not to provide the voltage that goes beyond absolute maximum ratings.

^{*1} Pulse width≤100µs, Duty ratio : 0.001 *2 40 to 60%RH, AC for 1 minute, f=60Hz

^{*3} For 10s



■ Model Line-up

Lead Form	Through-Hole	SMT G	ullwing	Rank mark	I _C [mA]
Package	100pcs/sleeve	100pcs/sleeve	2000pcs/reel	Kank mark	$(I_F=5mA, V_{CE}=5V, T_a=25^{\circ}C)$
	PC81100NSZ	PC81100NIZ	PC81100NIP	with or without	2.5 to 20.0
	PC81101NSZ	PC81101NIZ	PC81101NIP	A	3.0 to 6.0
	PC81102NSZ	PC81102NIZ	PC81102NIP	В	5.0 to 10.0
Model No.	PC81103NSZ	PC81103NIZ	PC81103NIP	С	7.5 to 15.0
	PC81105NSZ	PC81105NIZ	PC81105NIP	A or B	3.0 to 10.0
	PC81106NSZ	PC81106NIZ	PC81106NIP	B or C	5.0 to 15.0
	PC81108NSZ	PC81108NIZ	PC81108NIP	A, B or C	3.0 to 15.0

Please contact a local SHARP sales representative to inquire about production status and Lead-Free options.



Fig.1 Forward Current vs. Ambient Temperature

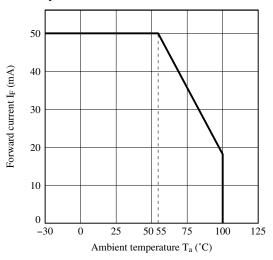


Fig.3 Collector Power Dissipation vs. Ambient Temperature

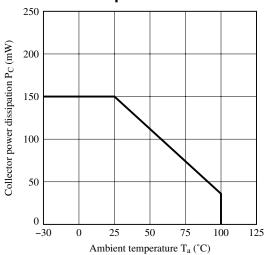


Fig.5 Peak Forward Current vs. Duty Ratio

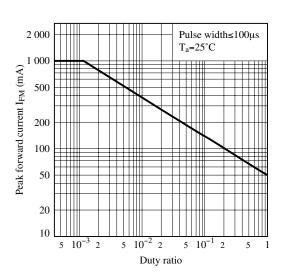


Fig.2 Diode Power Dissipation vs.
Ambient Temperature

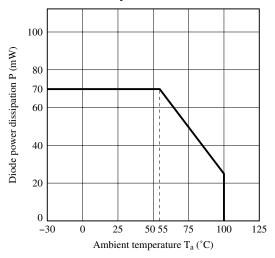


Fig.4 Total Power Dissipation vs. Ambient Temperature

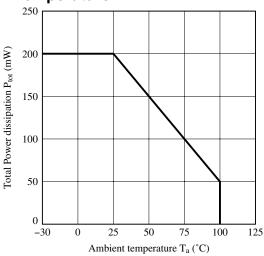


Fig.6 Forward Current vs. Forward Voltage

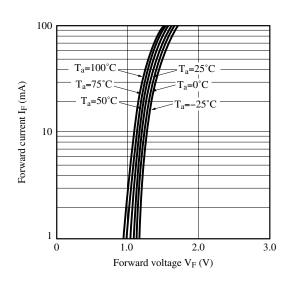




Fig.7 Current Transfer Ratio vs. Forward Current

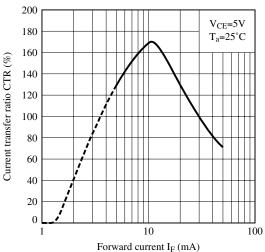


Fig.9 Relative Current Transfer Ratio vs. Ambient Temperature

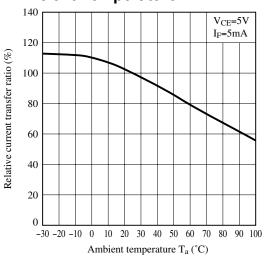


Fig.11 Collector Dark Current vs. Ambient Temperature

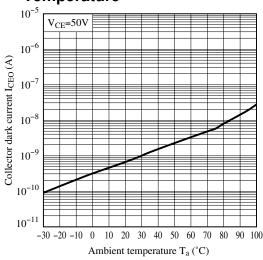


Fig.8 Collector Current vs. Collector-emitter Voltage

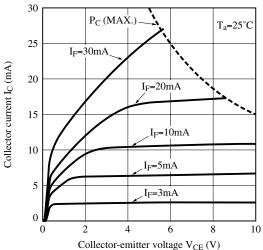


Fig.10 Collector - emitter Saturation Voltage vs. Ambient Temperature

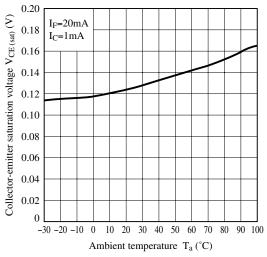


Fig.12 Response Time vs. Load Resistance (saturation region)

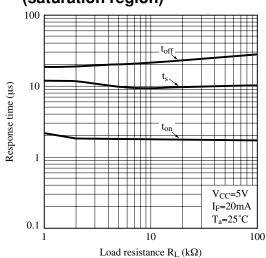




Fig.13 Response Time vs. Load Resistance (active region)

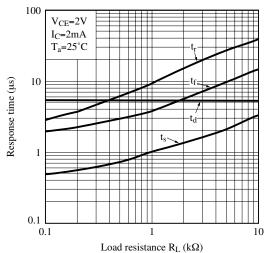
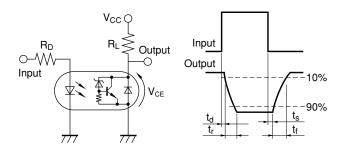


Fig.14 Test Circuit for Response Time



Please refer to the conditions in Fig.12 and Fig.13

Fig.15 Frequency Response

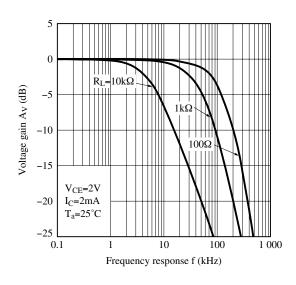
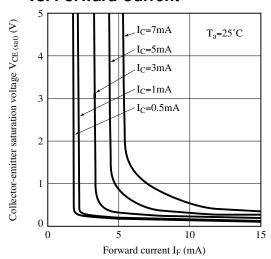


Fig.16 Collector-emitter Saturation Voltage vs. Forward Current



Remarks: Please be aware that all data in the graph are just for reference and not for guarantee.



■ Design Considerations

Design guide

While operating at I_F<5.0mA, CTR variation may increase.

Please make design considering this fact.

This product is not designed against irradiation and incorporates non-coherent IRED.

The collector-emitter voltage has negative resistance characteristics since this device has built-in base-emitter resistor.

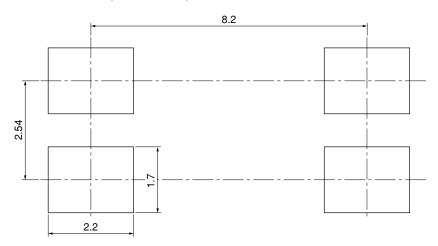
Therefore, please be careful not to provide the voltage that goes beyond absolute maximum ratings.

Degradation

In general, the emission of the IRED used in photocouplers will degrade over time.

In the case of long term operation, please take the general IRED degradation (50% degradation over 5years) into the design consideration.

Recommended Foot Print (reference)



(Unit: mm)

[☆] For additional design assistance, please review our corresponding Optoelectronic Application Notes.



■ Manufacturing Guidelines

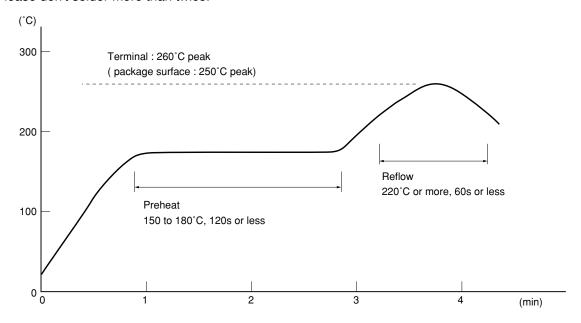
Soldering Method

Reflow Soldering:

Reflow soldering should follow the temperature profile shown below.

Soldering should not exceed the curve of temperature profile and time.

Please don't solder more than twice.



Flow Soldering:

Due to SHARP's double transfer mold construction submersion in flow solder bath is allowed under the below listed guidelines.

Flow soldering should be completed below 270°C and within 10s.

Preheating is within the bounds of 100 to 150°C and 30 to 80s.

Please don't solder more than twice.

Hand soldering

Hand soldering should be completed within 3s when the point of solder iron is below 400°C.

Please don't solder more than twice.

Other notices

Please test the soldering method in actual condition and make sure the soldering works fine, since the impact on the junction between the device and PCB varies depending on the tooling and soldering conditions.



Cleaning instructions

Solvent cleaning:

Solvent temperature should be 45°C or below Immersion time should be 3minutes or less

Ultrasonic cleaning:

The impact on the device varies depending on the size of the cleaning bath, ultrasonic output, cleaning time, size of PCB and mounting method of the device.

Therefore, please make sure the device withstands the ultrasonic cleaning in actual conditions in advance of mass production.

Recommended solvent materials:

Ethyl alcohol, Methyl alcohol and Isopropyl alcohol

In case the other type of solvent materials are intended to be used, please make sure they work fine in actual using conditions since some materials may erode the packaging resin.

Presence of ODC

This product shall not contain the following materials.

And they are not used in the production process for this device.

Regulation substances:CFCs, Halon, Carbon tetrachloride, 1.1.1-Trichloroethane (Methylchloroform)

Specific brominated flame retardants such as the PBBOs and PBBs are not used in this product at all.

Sheet No.: D2-A03801EN



■ Package specification

Sleeve package

Package materials

Sleeve: HIPS (with anti-static material)

Stopper: Styrene-Elastomer

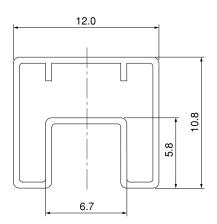
Package method

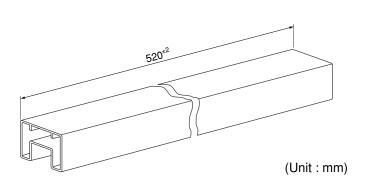
MAX. 100pcs of products shall be packaged in a sleeve. Both ends shall be closed by tabbed and tabless stoppers.

The product shall be arranged in the sleeve with its anode mark on the tabless stopper side.

MAX. 20 sleeves in one case.

Sleeve outline dimensions







● Tape and Reel package

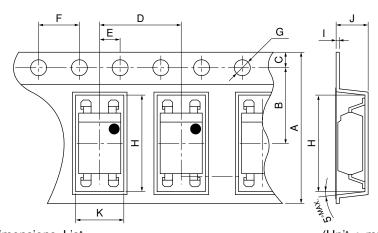
Package materials

Carrier tape : PS

Cover tape : PET (three layer system)

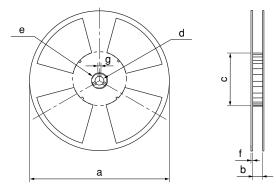
Reel: PS

Carrier tape structure and Dimensions



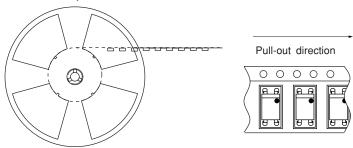
(Unit: mm) Dimensions List C D E F G 16.0±0.3 7.5^{±0.1} 1.75^{±0.1} 8.0^{±0.1} $2.0^{\pm0.1}$ $4.0^{\pm0.1}$ $\phi 1.5^{+0.1}_{-0}$ Η K $4.2^{\pm0.1}$ $10.4^{\pm0.1}$ $0.4^{\pm0.05}$ $5.1^{\pm0.1}$

Reel structure and Dimensions



Dime	nsio	ns List	(Unit: mm)		
a	l	b	с	d	
33	330 17.5 ^{±1.5}		100±1.0	13 ^{±0.5}	
e	;	f	g		
23±	:1.0	2.0 ^{±0.5}	2.0 ^{±0.5}		

Direction of product insertion



[Packing: 2 000pcs/reel]



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